

1M x 4-Bit Dynamic RAM

HYB 314400BJ/BJL-50/-60/-70

Advanced Information

- 1 048 576 words by 4-bit organization
- 0 to 70 °C operating temperature
- Fast Page Mode Operation
- Performance:

		-50	-60	-70	
t_{RAC}	$\overline{RAS}$ access time	50	60	70	ns
t_{CAC}	$\overline{CAS}$ access time	13	15	20	ns
t_{AA}	Access time from address	25	30	35	ns
t_{RC}	Read/Write cycle time	95	110	130	ns
t_{PC}	Fast page mode cycle time	35	40	45	ns

- Fast access and cycle time
Single + 3.3 V (± 0.3 V) supply with a built-in V_{bb} generator
- Low power dissipation
max. 252 mW active (-50 version)
max. 216 mW active (-60 version)
max. 198 mW active (-70 version)
- Standby power dissipation:
7,2 mW max. standby (LVTTL)
3,6 mW max. standby (LVCMOS)
720 μ W max. standby (LVCMOS) for Low Power Versions
- Output unlatched at cycle end allows two-dimensional chip selection
- Read, write, read-modify write, CAS-before- $\overline{RAS}$ refresh, $\overline{RAS}$ -only refresh, hidden refresh and test mode capability
- All inputs and outputs LVTTL-compatible
- 1024 refresh cycles / 16 ms
- 1024 refresh cycles / 128 ms for Low Power Version
- Plastic Packages: P-SOJ-26/20-5 with 300 mil width

The HYB 314400BJ/BJL is the new generation dynamic RAM organized as 1 048 576 words by 4-bit. The HYB 314400BJ/BJL utilizes CMOS silicon gate process as well as advances circuit techniques to provide wide operation margins, both internally and for the system user. Multiplexed address inputs permit the HYB 314400BJ/BJL to be packed in a standard plastic P-SOJ-26/20 package. This package size provides high system bit densities and is compatible with commonly used automatic testing and insertion equipment. System oriented features include single + 3.3 V (± 0.3 V) power supply, direct interfacing with high performance logic device families.

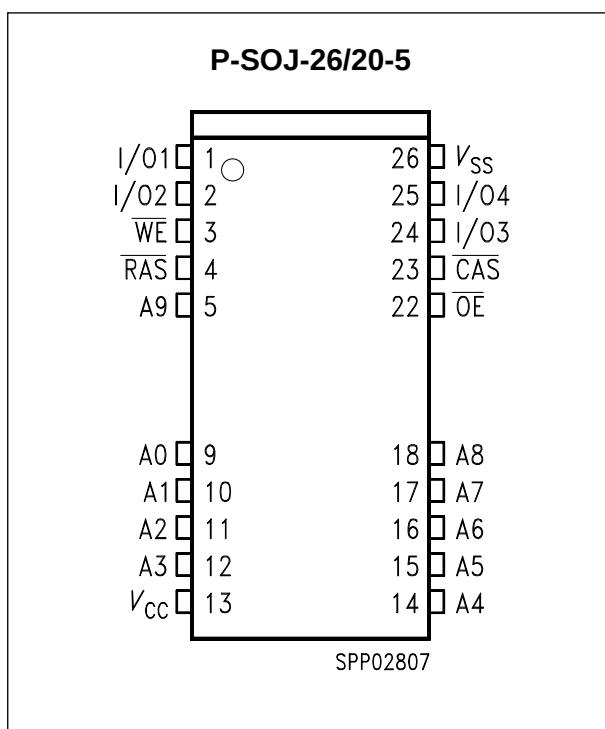
Ordering Information

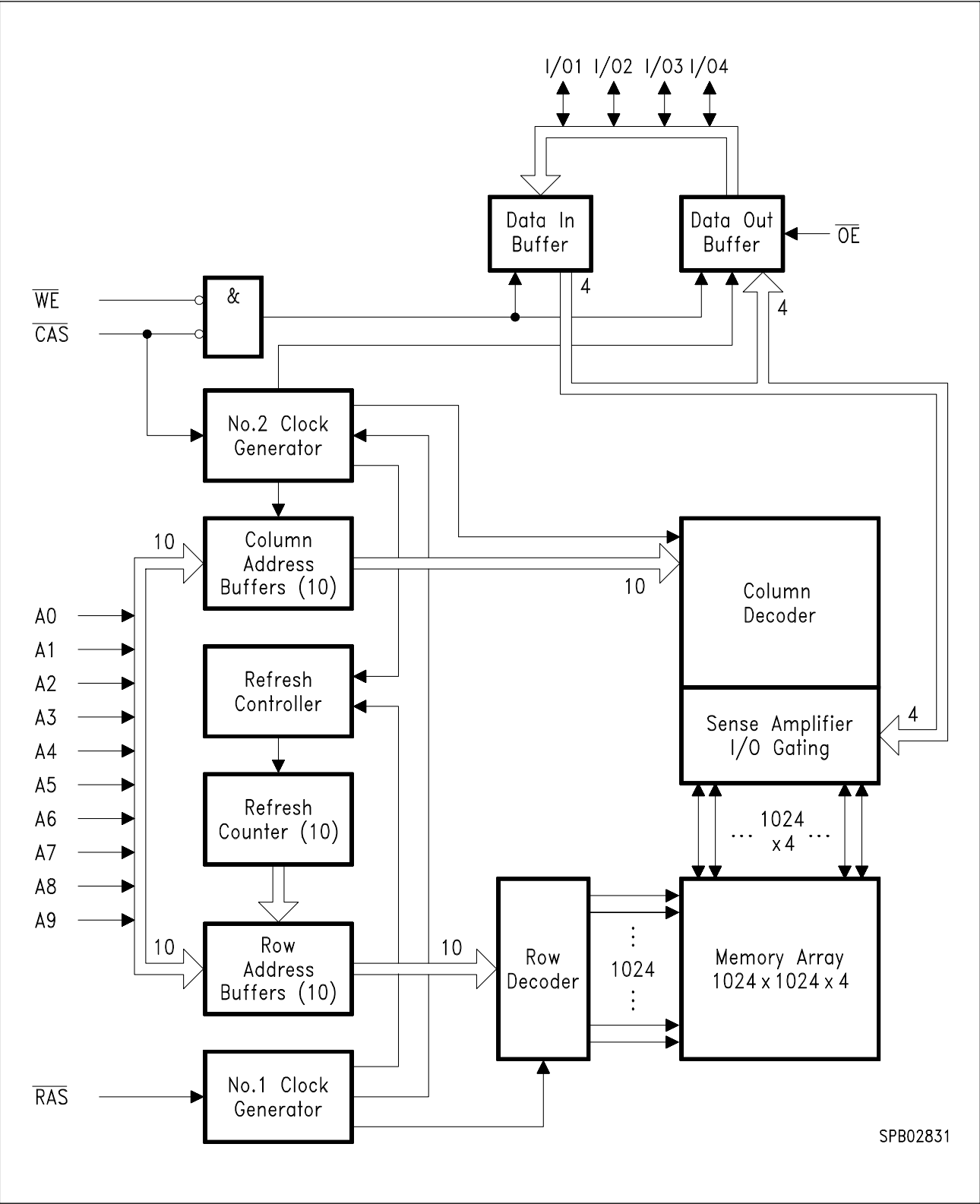
Type	Ordering Code	Package	Descriptions
HYB 314400BJ-50	Q67100-Q2027	P-SOJ-26/20-5	3.3 V DRAM (access time 50 ns)
HYB 314400BJ-60	Q67100-Q2029	P-SOJ-26/20-5	3.3 V DRAM (access time 60 ns)
HYB 314400BJ-70	Q67100-Q2031	P-SOJ-26/20-5	3.3 V DRAM (access time 70 ns)
HYB 314400BJL-50	on request	P-SOJ-26/20-5	3.3 V Low Power DRAM (access time 50 ns)
HYB 314400BJL-60	on request	P-SOJ-26/20-5	3.3 V Low Power DRAM (access time 60 ns)
HYB 314400BJL-70	on request	P-SOJ-26/20-5	3.3 V Low Power DRAM (access time 70 ns)

Pin Names

A0-A9	Address Input
$\overline{\text{RAS}}$	Row Address Strobe
$\overline{\text{CAS}}$	Column Address Strobe
$\overline{\text{WE}}$	Read/Write Input
$\overline{\text{OE}}$	Output Enable
I/O1 - I/O4	Data Input/Output
V_{CC}	Power Supply (+ 3.3 V)
V_{SS}	Ground (0 V)
N.C.	No Connection

Pin Configuration (top view)





Block Diagram

Absolute Maximum Ratings

Operating temperature range 0 to 70 °C
 Storage temperature range – 55 to + 150 °C
 Input/output voltage – 1 to min ($V_{CC} + 0.5$, 4.6) V
 Power Supply voltage – 1 to + 4.6 V
 Data out current (short circuit) 50 mA

Note: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage of the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC Characteristics

$T_A = 0$ to 70 °C, $V_{SS} = 0$ V, $V_{CC} = 3.3$ V $\pm$ 0.3 V, $t_T = 5$ ns

Parameter	Symbol	Limit Values		Unit	Test Condition
		min.	max.		
Input high voltage	V_{IH}	2.0	$V_{CC} + 0.5$	V	1)
Input low voltage	V_{IL}	– 1.0	0.8	V	1)
TTL Output high voltage ($I_{OUT} = -2$ mA)	V_{OH}	2.4	–	V	1)
TTL Output low voltage ($I_{OUT} = 2$ mA)	V_{OH}	–	0.4	V	1)
CMOS Output high voltage ($I_{OUT} = -100$ μ A)	V_{OH}	$V_{CC} - 0.2$	–	V	
CMOS Output low voltage ($I_{OUT} = 100$ μ A)	V_{OH}	–	0.2	V	
Input leakage current, any input (0 V < V_{in} < $V_{CC} + 0.3$ V, all other input = 0 V)	$I_{I(L)}$	– 10	10	μ A	1)
Output leakage current (DO is disabled, $0 < V_{OUT} < V_{CC}$)	$I_{O(L)}$	– 10	10	μ A	1)
Average V_{CC} supply current –50 version –60 version –70 version	I_{CC1}	– – –	70 60 55	mA	2) 3)4)
Standby V_{CC} supply current ($RAS = CAS = WE = V_{IH}$)	I_{CC2}	–	2	mA	–
Average V_{CC} supply current during $\overline{RAS}$ -only refresh cycles –50 version –60 version –70 version	I_{CC3}	– – –	70 60 55	mA	2)4)
Average V_{CC} supply current during fast page mode operation –50 version –60 version –70 version	I_{CC4}	– – –	50 45 40	mA	2) 3)4)
Standby V_{CC} supply current ($RAS = CAS = WE = V_{CC} - 0.2$ V)	I_{CC5}	–	1 200	mA μ A	1) L-version

DC Characteristics (cont'd)

$T_A = 0 \text{ to } 70^\circ\text{C}$, $V_{SS} = 0 \text{ V}$, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $t_T = 5 \text{ ns}$

Parameter	Symbol	Limit Values		Unit	Test Condition
		min.	max.		
Average V_{CC} supply current during $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh mode -50 version -60 version -70 version	I_{CC6}	— — —	70 60 55	mA	2)4)
For Low Power Version only: Battery backup current (average power supply current in battery backup mode): ($\overline{\text{CAS}} = \overline{\text{CAS}}$ before $\overline{\text{RAS}}$ cycling or 0.2 V, $\overline{\text{WE}} = V_{CC} - 0.2 \text{ V}$ or 0.2 V, $\text{A0 to A10} = V_{CC} - 0.2 \text{ V}$ or 0.2 V; $\text{DI} = V_{CC} - 0.2 \text{ V}$ or 0.2 V or open, $t_{RC} = 125 \mu\text{s}$, $t_{RAS} = t_{RAS} \text{ min} = 1 \mu\text{s}$)	I_{CC7}	—	250	μA	—

Capacitance

$T_A = 0 \text{ to } 70^\circ\text{C}$; $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$; $f = 1 \text{ MHz}$

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Input capacitance (A0 to A9)	C_{I1}	—	5	pF
Input capacitance ($\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$)	C_{I2}	—	7	pF
Output capacitance (IO1 to IO4)	C_{I0}	—	7	pF

AC Characteristics ⁵⁾⁶⁾

$T_A = 0 \text{ to } 70^\circ\text{C}$, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $t_T = 5 \text{ ns}$

Parameter	Symbol	Limit Values						Unit	Note
		-50		-60		-70			
		min.	max.	min.	max.	min.	max.		

Common Parameters

Random read or write cycle time	t_{RC}	95	—	110	—	130	—	ns	
RAS precharge time	t_{RP}	35	—	40	—	50	—	ns	
RAS pulse width	t_{RAS}	50	10 k	60	10 k	70	10 k	ns	
CAS pulse width	t_{CAS}	13	10 k	15	10 k	20	10 k	ns	
Row address setup time	t_{ASR}	0	—	0	—	0	—	ns	
Row address hold time	t_{RAH}	8	—	10	—	10	—	ns	
Column address setup time	t_{ASC}	0	—	0	—	0	—	ns	
Column address hold time	t_{CAH}	10	—	15	—	15	—	ns	
RAS to CAS delay time	t_{RCD}	18	37	20	45	20	50		
RAS to column address delay time	t_{RAD}	13	25	15	30	15	35	ns	
RAS hold time	t_{RSH}	13		15	—	20	—	ns	
CAS hold time	t_{CSH}	50		60	—	70	—	ns	
CAS to RAS precharge time	t_{CRP}	5	—	5	—	5	—	ns	
Transition time (rise and fall)	t_T	3	50	3	50	3	50	ns	7
Refresh period	t_{REF}	—	16	—	16	—	16	ms	
Refresh period for L-version	t_{REF}	—	128	—	128	—	128	ms	

Read Cycle

Access time from RAS	t_{RAC}	—	50	—	60	—	70	ns	8, 9
Access time from CAS	t_{CAC}	—	13	—	15	—	20	ns	8, 9
Access time from column address	t_{AA}	—	25	—	30	—	35	ns	8,10
OE access time	t_{OEA}	—	13	—	15	—	20	ns	
Column address to RAS lead time	t_{RAL}	25	—	30	—	35	—	ns	
Read command setup time	t_{RCS}	0	—	0	—	0	—	ns	
Read command hold time	t_{RCH}	0	—	0	—	0	—	ns	11

AC Characteristics (cont'd) ⁵⁾⁶⁾

$T_A = 0 \text{ to } 70^\circ\text{C}$, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $t_T = 5 \text{ ns}$

Parameter	Symbol	Limit Values						Unit	Note
		-50		-60		-70			
		min.	max.	min.	max.	min.	max.		
Read command hold time referenced to $\overline{\text{RAS}}$	t_{RRH}	0	—	0	—	0	—	ns	11
$\overline{\text{CAS}}$ to output in low-Z	t_{CLZ}	0	—	0	—	0	—	ns	8
Output buffer turn-off delay	t_{OFF}	0	13	0	15	0	20	ns	12
Output buffer turn-off delay from $\overline{\text{OE}}$	t_{OEZ}	0	13	0	15	0	20	ns	12
Data to $\overline{\text{OE}}$ low delay	t_{DZO}	0	—	0	—	0	—	ns	13
$\overline{\text{CAS}}$ high to data delay	t_{CDD}	13	—	15	—	20	—	ns	14
$\overline{\text{OE}}$ high to data delay	t_{ODD}	13	—	15	—	20	—	ns	14

Write Cycle

Write command hold time	t_{WCH}	8	—	10	—	10	—	ns	
Write command pulse width	t_{WP}	8	—	10	—	10	—	ns	
Write command setup time	t_{WCS}	0	—	0	—	0	—	ns	15
Write command to $\overline{\text{RAS}}$ lead time	t_{RWL}	13	—	15	—	20	—	ns	
Write command to $\overline{\text{CAS}}$ lead time	t_{CWL}	13	—	15	—	20	—	ns	
Data setup time	t_{DS}	0	—	0	—	0	—	ns	16
Data hold time	t_{DH}	10	—	10	—	15	—	ns	16
Data to $\overline{\text{CAS}}$ low delay	t_{DZC}	0	—	0	—	0	—	ns	13

Read-Modify-Write Cycle

Read-write cycle time	t_{RWC}	131	—	150	—	180	—	ns	
$\overline{\text{RAS}}$ to $\overline{\text{WE}}$ delay time	t_{RWD}	68	—	80	—	95	—	ns	15
$\overline{\text{CAS}}$ to $\overline{\text{WE}}$ delay time	t_{CWD}	31	—	35	—	45	—	ns	15
Column address to $\overline{\text{WE}}$ delay time	t_{AWD}	43	—	50	—	60	—	ns	15
$\overline{\text{OE}}$ command hold time	t_{OEH}	13	—	15	—	20	—	ns	

AC Characteristics (cont'd) ⁵⁾⁶⁾

$T_A = 0 \text{ to } 70 \text{ }^\circ\text{C}$, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $t_T = 5 \text{ ns}$

Parameter	Symbol	Limit Values						Unit	Note
		-50		-60		-70			
		min.	max.	min.	max.	min.	max.		

Fast Page Mode Cycle

Fast page mode cycle time	t_{PC}	35	–	40	–	45	–	ns	
$\overline{\text{CAS}}$ precharge time	t_{CP}	10	–	10	–	10	–	ns	
Access time from $\overline{\text{CAS}}$ precharge	t_{CPA}	–	30	–	35	–	40	ns	7
RAS pulse width	t_{RAS}	50	200 k	60	200 k	70	200 k	ns	
$\overline{\text{CAS}}$ precharge to $\overline{\text{RAS}}$ Delay	t_{RHCP}	30	–	35	–	40	–	ns	

Fast Page Mode Read-Modify-Write Cycle

Fast page mode read-write cycle time	t_{PRWC}	71	–	80	–	95	–	ns	
$\overline{\text{CAS}}$ precharge to WE	t_{CPWD}	48	–	55	–	65	–	ns	

$\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Refresh Cycle

$\overline{\text{CAS}}$ setup time	t_{CSR}	10	–	10	–	10	–	ns	
$\overline{\text{CAS}}$ hold time	t_{CHR}	10	–	10	–	10	–	ns	
RAS to $\overline{\text{CAS}}$ precharge time	t_{RPC}	5	–	5	–	5	–	ns	
Write to $\overline{\text{RAS}}$ precharge time	t_{WRP}	10	–	10	–	10	–	ns	
Write hold time referenced to $\overline{\text{RAS}}$	t_{WRH}	10	–	10	–	10	–	ns	

$\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Counter Test Cycle

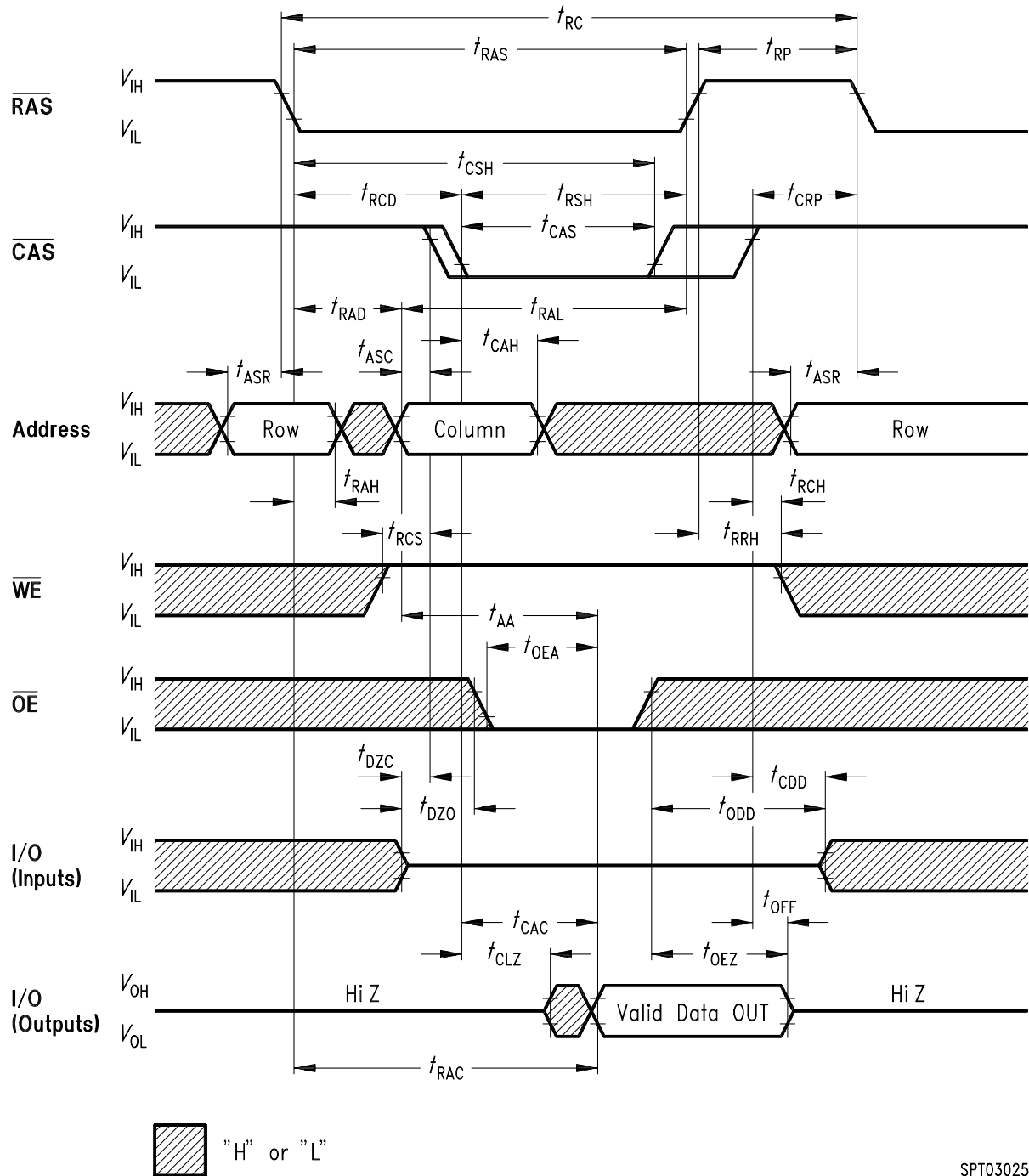
$\overline{\text{CAS}}$ precharge time	t_{CPT}	35	–	40	–	40	–	ns	
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Test Mode

Write command setup time	t_{WTS}	10	–	10	–	10	–	ns	
Write command hold time	t_{WTH}	10	–	10	–	10	–	ns	

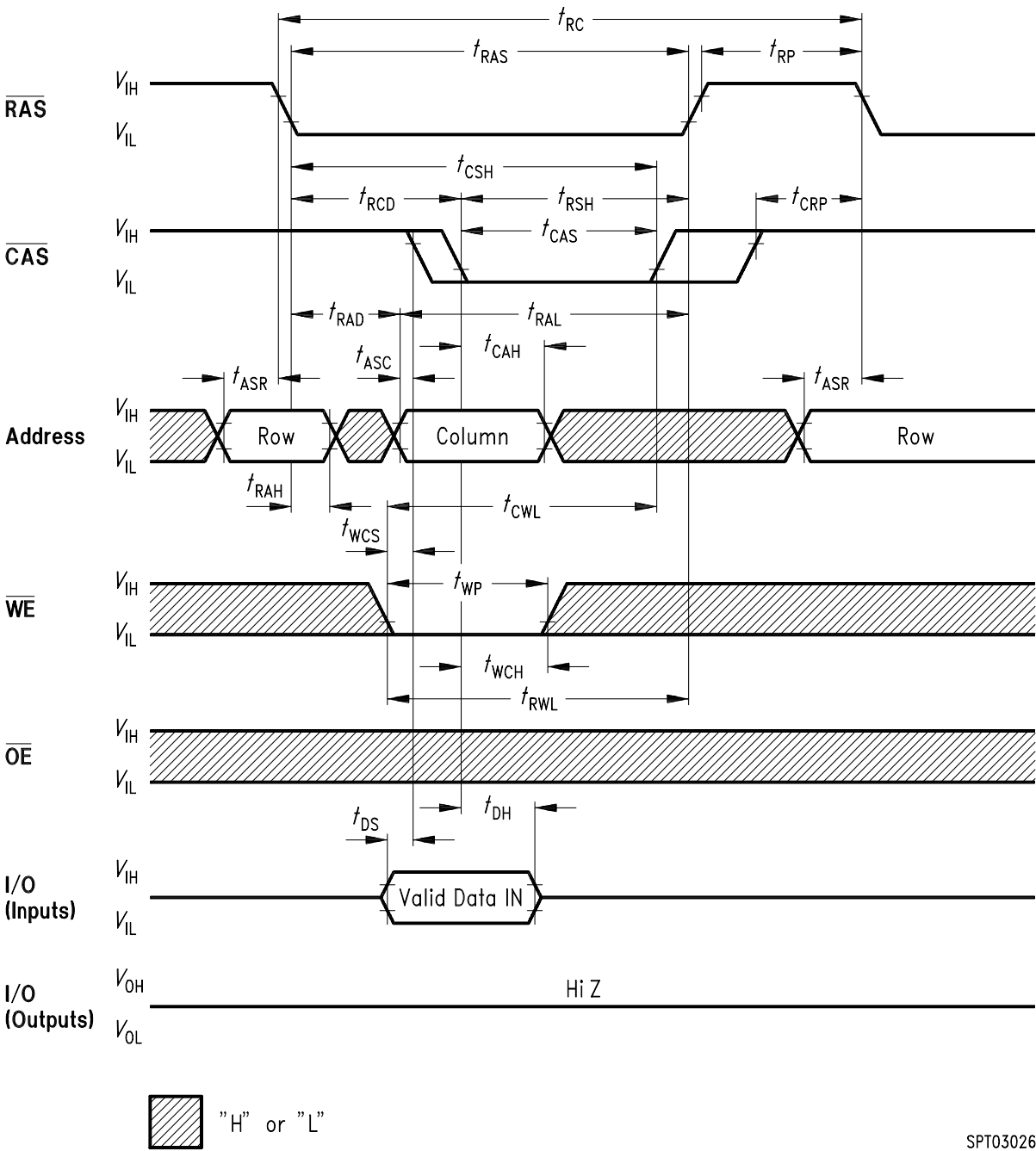
Notes:

- 1) All voltages are referenced to V_{SS} .
- 2) I_{CC1} , I_{CC3} , I_{CC4} and I_{CC6} depend on cycle rate.
- 3) I_{CC1} and I_{CC4} depend on output loading. Specified values are measured with the output open.
- 4) Address can be changed once or less while $\overline{RAS} = V_{IL}$. In the case of I_{CC4} it can be changed once or less during a fast page mode cycle (t_{PC}).
- 5) An initial pause of 200 μs is required after power-up followed by 8 $\overline{RAS}$ cycles of which at least one cycle has to be a refresh cycle, before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 CAS-before-RAS initialization cycles instead of 8 $\overline{RAS}$ cycles are required.
- 6) AC measurements assume $t_T = 5$ ns.
- 7) $V_{IH (min.)}$ and $V_{IL (max.)}$ are reference levels for measuring timing of input signals. Transition times are also measured between V_{IH} and V_{IL} .
- 8) Measured with a load equivalent to 100 pF and at $V_{OH} = 2.0$ V ($I_{OH} = -2$ mA), $V_{OL} = 0.8$ V ($I_{OL} = 2$ mA).
- 9) Operation within the $t_{RCD (max.)}$ limit ensures that $t_{RAC (max.)}$ can be met. $t_{RCD (max.)}$ is specified as a reference point only: If t_{RCD} is greater than the specified $t_{RCD (max.)}$ limit, then access time is controlled by t_{CAC} .
- 10) Operation within the $t_{RAD (max.)}$ limit ensures that $t_{RAC (max.)}$ can be met. $t_{RAD (max.)}$ is specified as a reference point only: If t_{RAD} is greater than the specified $t_{RAD (max.)}$ limit, then access time is controlled by t_{AA} .
- 11) Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
- 12) $t_{OFF (max.)}$ and $t_{OEZ (max.)}$ define the time at which the outputs achieve the open-circuit condition and are not referenced to output voltage levels.
- 13) Either t_{DZC} or t_{DZO} must be satisfied.
- 14) Either t_{CDD} or t_{ODD} must be satisfied.
- 15) t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} > t_{WCS (min.)}$, the cycle is an early write cycle and the I/O pin will remain open-circuit (high impedance) through the entire cycle; if $t_{RWD} > t_{RWD (min.)}$, $t_{CWD} > t_{CWD (min.)}$, $t_{AWD} > t_{AWD (min.)}$ and $t_{CPWD} > t_{CPWD (min.)}$, the cycle is a read-write cycle and I/O pins will contain data read from the selected cells. If neither of the above sets of conditions is satisfied, the condition of the I/O pins (at access time) is indeterminate.
- 16) These parameters are referenced to the $\overline{CAS}$ leading edge in early write cycles and to the $\overline{WE}$ leading edge in read-write cycles.



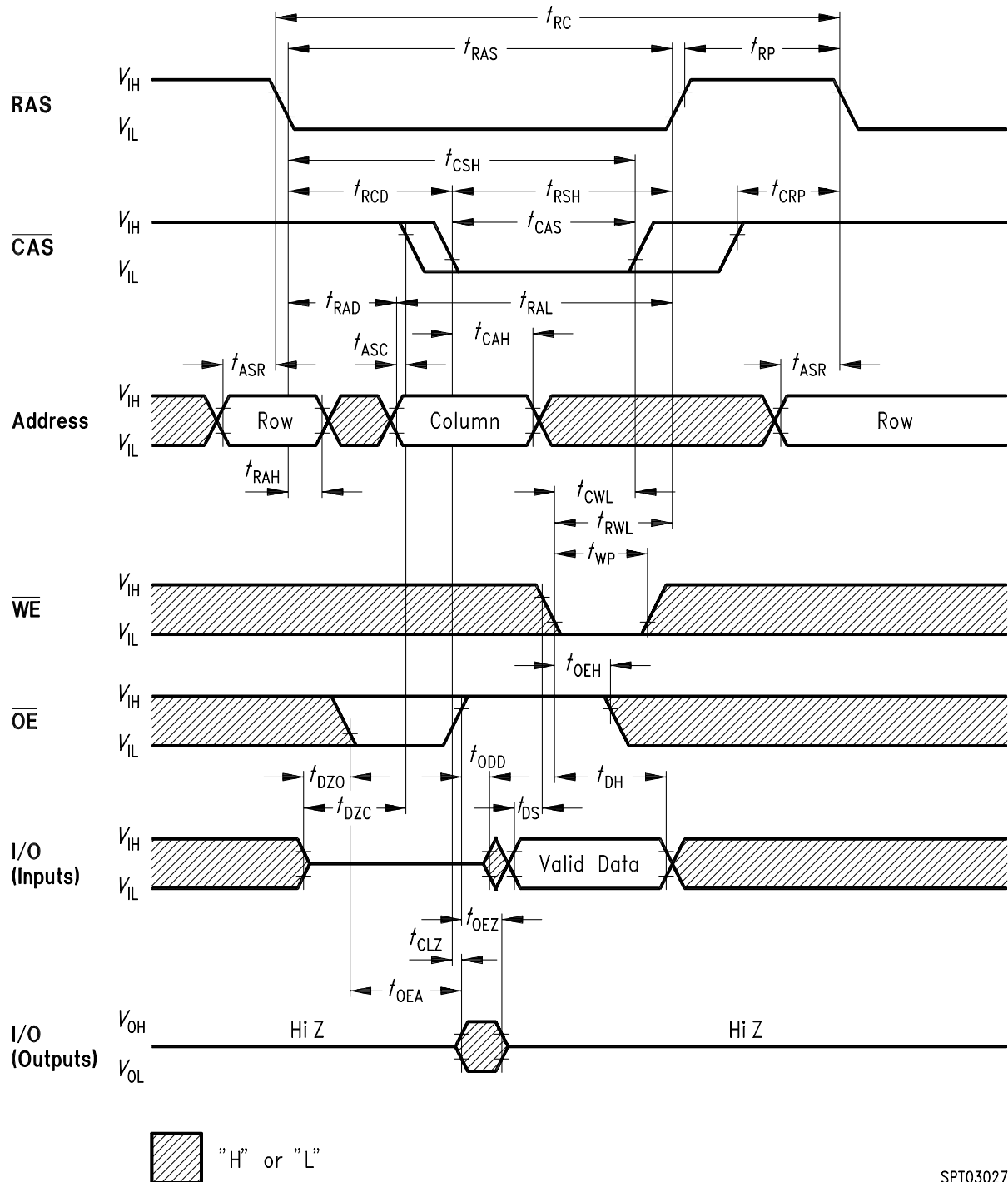
SPT03025

Read Cycle



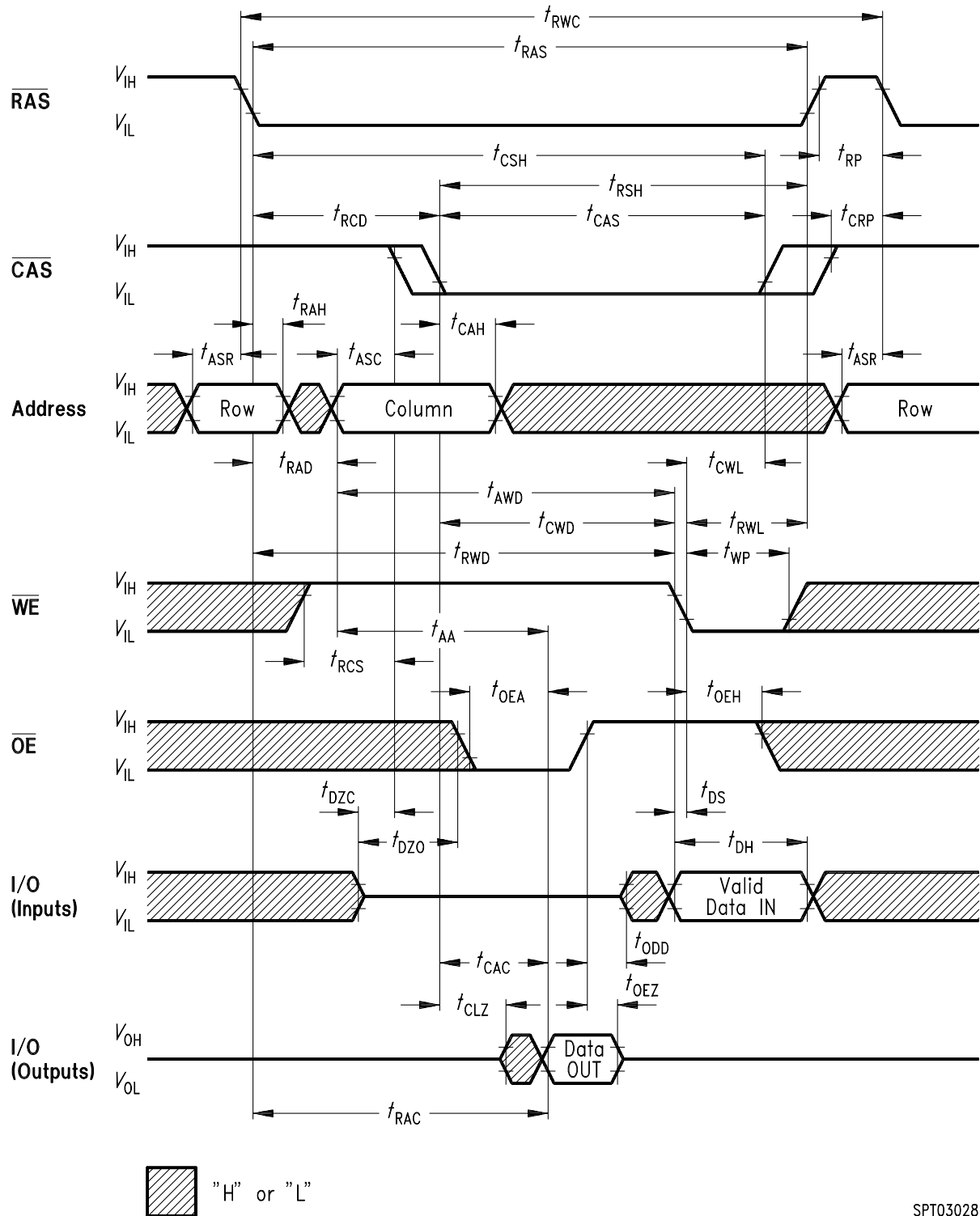
SPT03026

Write Cycle (Early Write)



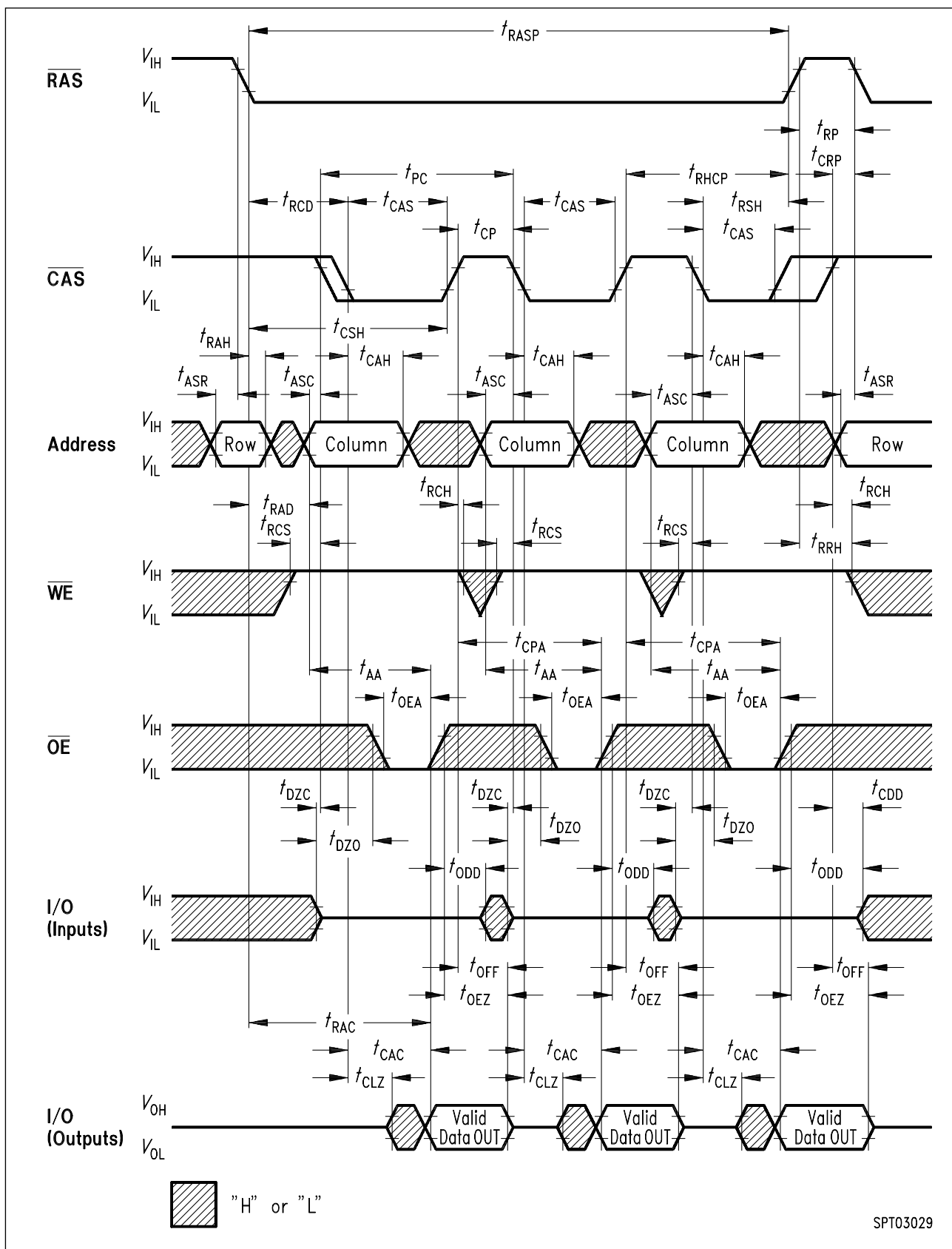
SPT03027

Write Cycle (OE Controlled Write)

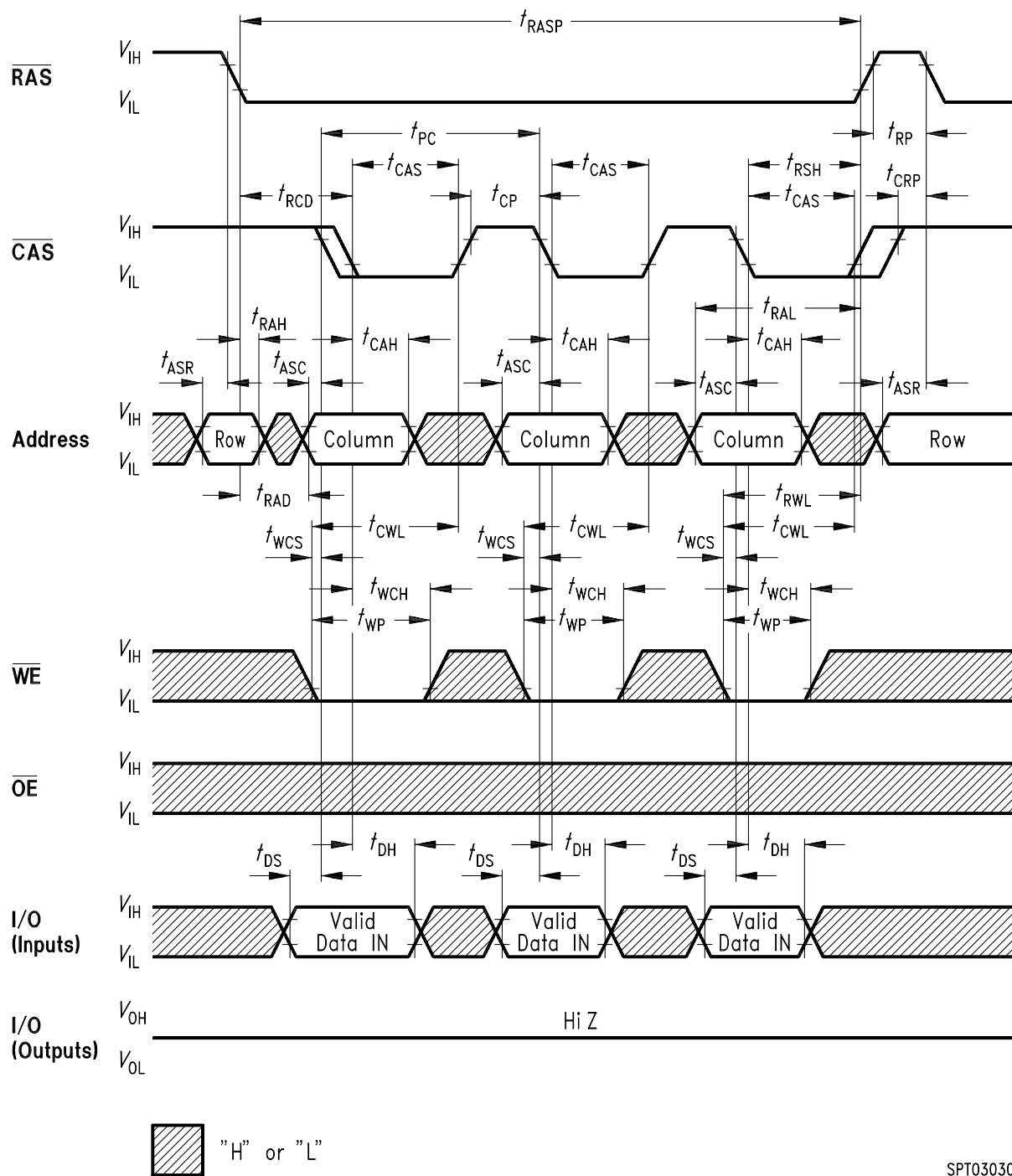


SPT03028

Read-Write (Read-Modify-Write) Cycle

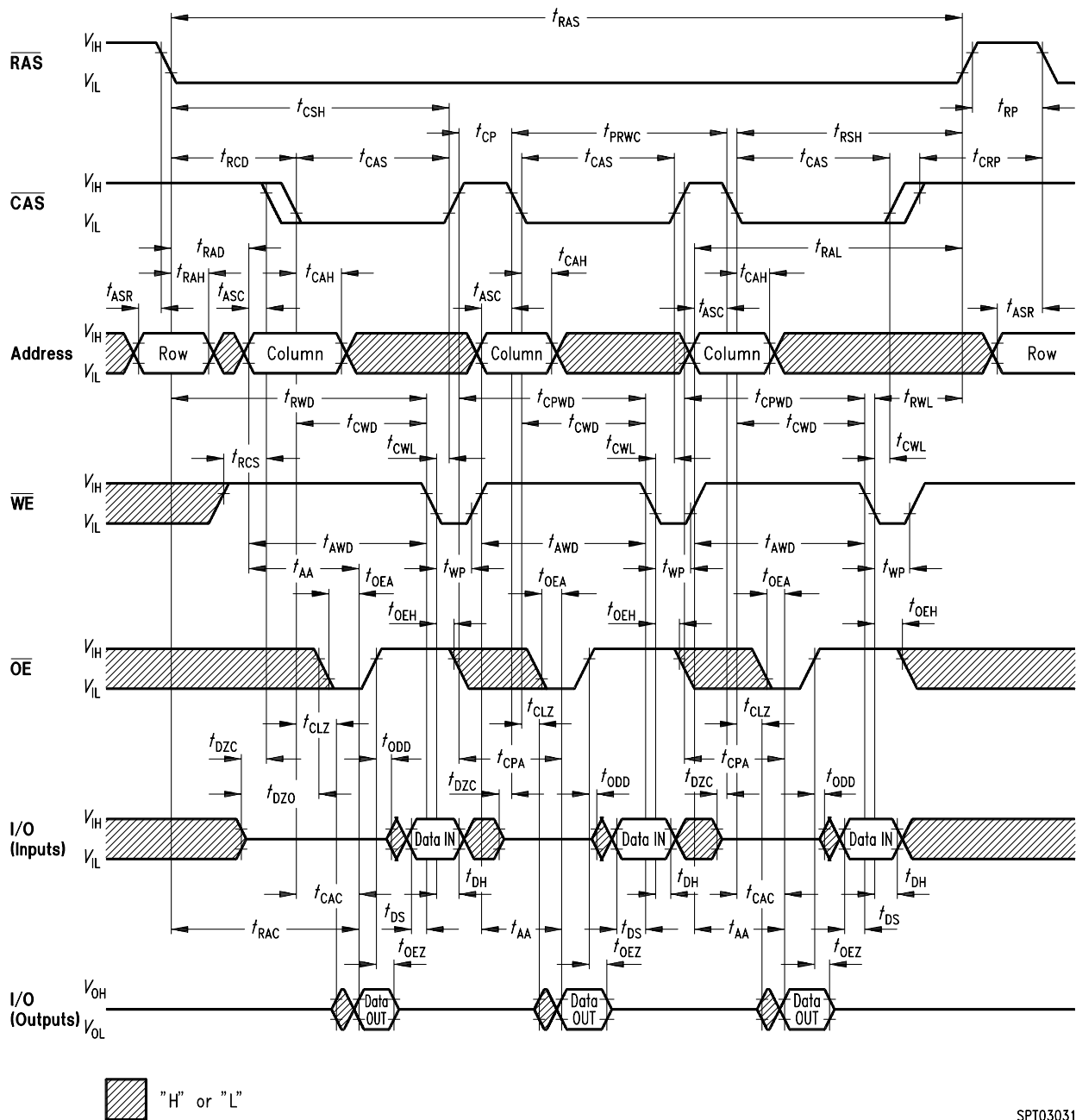


Fast Page Mode Read Cycle



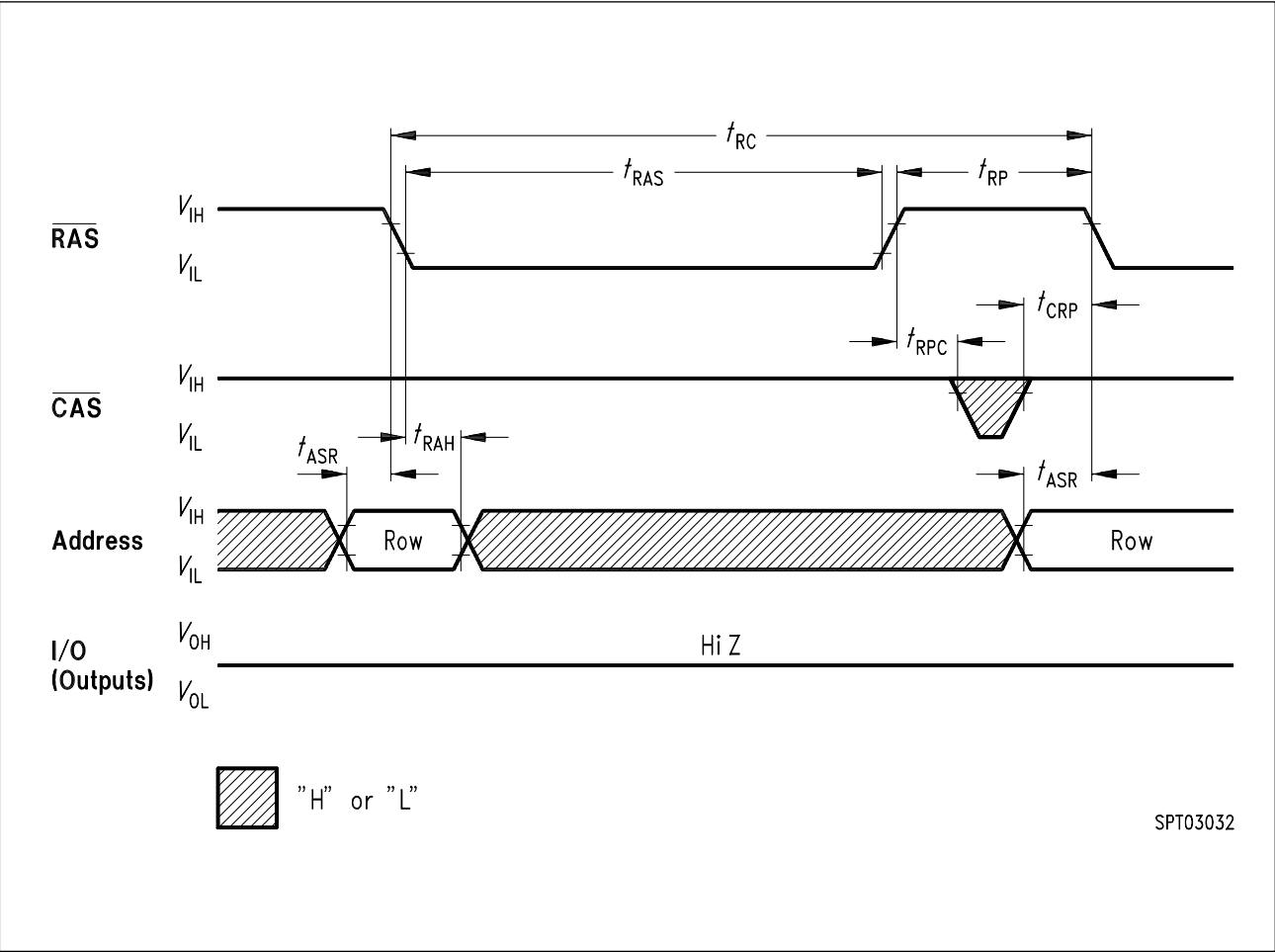
SPT03030

Fast Page Mode Early Write Cycle

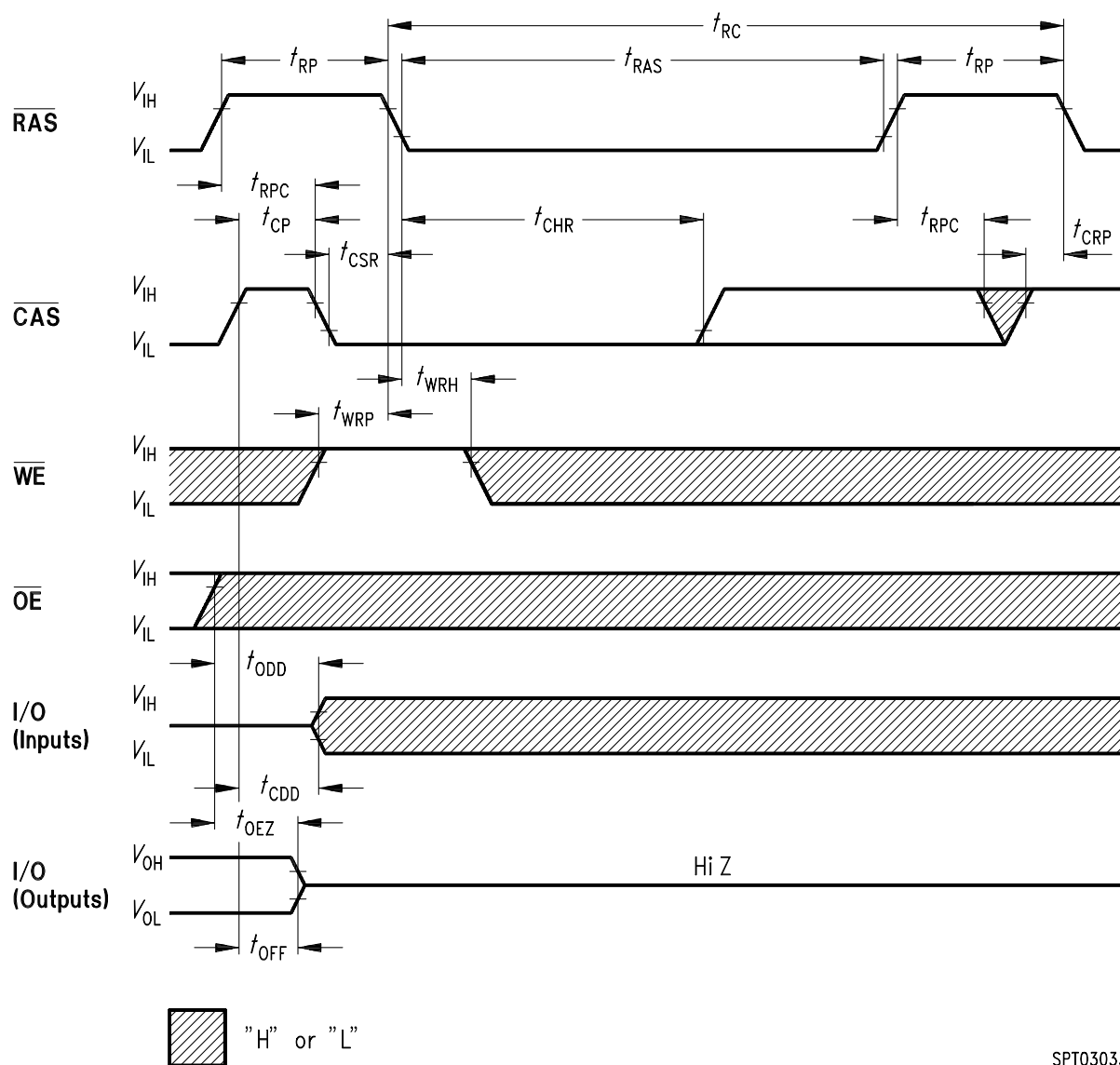


SPT03031

Fast Page Mode Read-Modify-Write Cycle

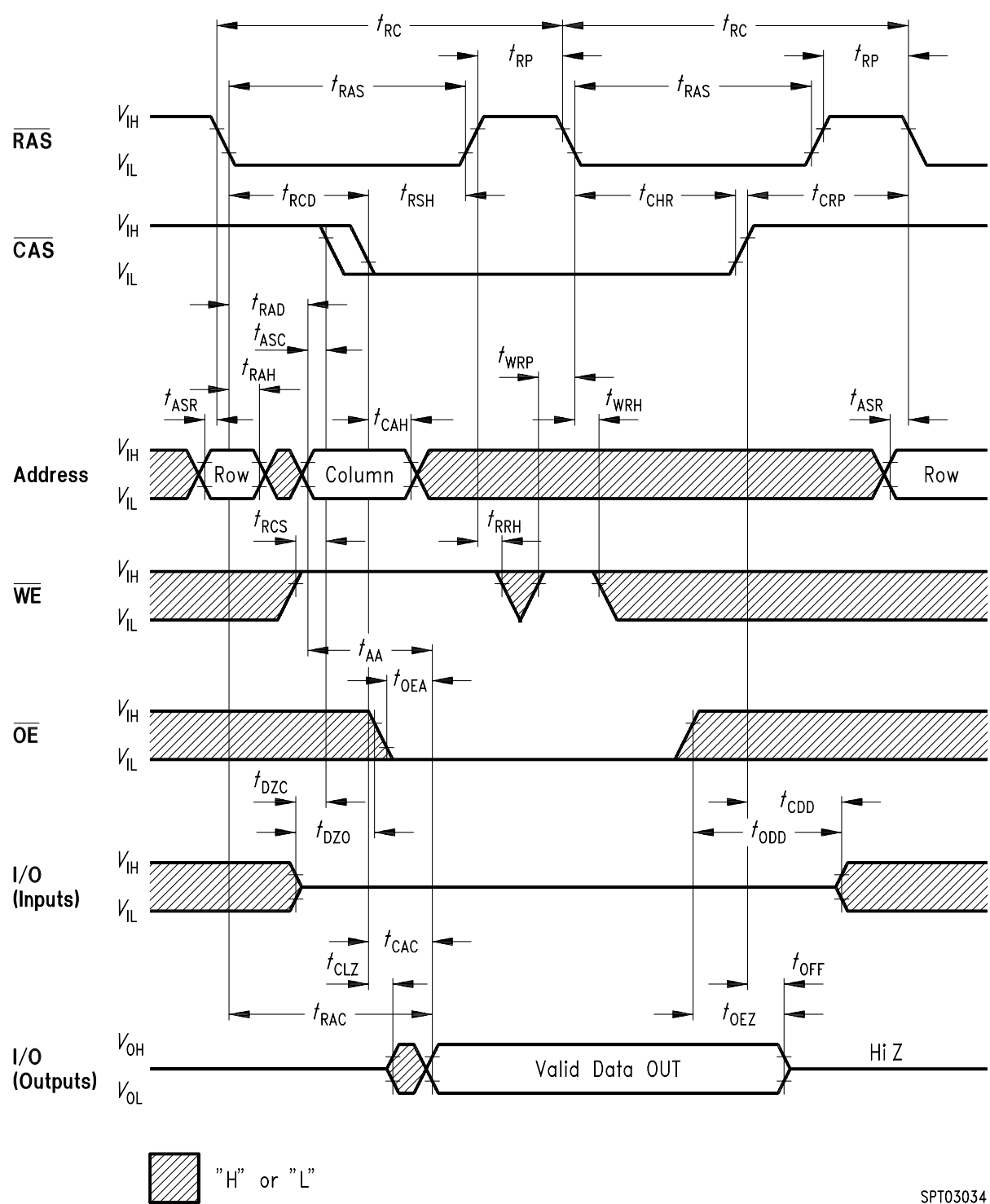


RAS-Only Refresh Cycle



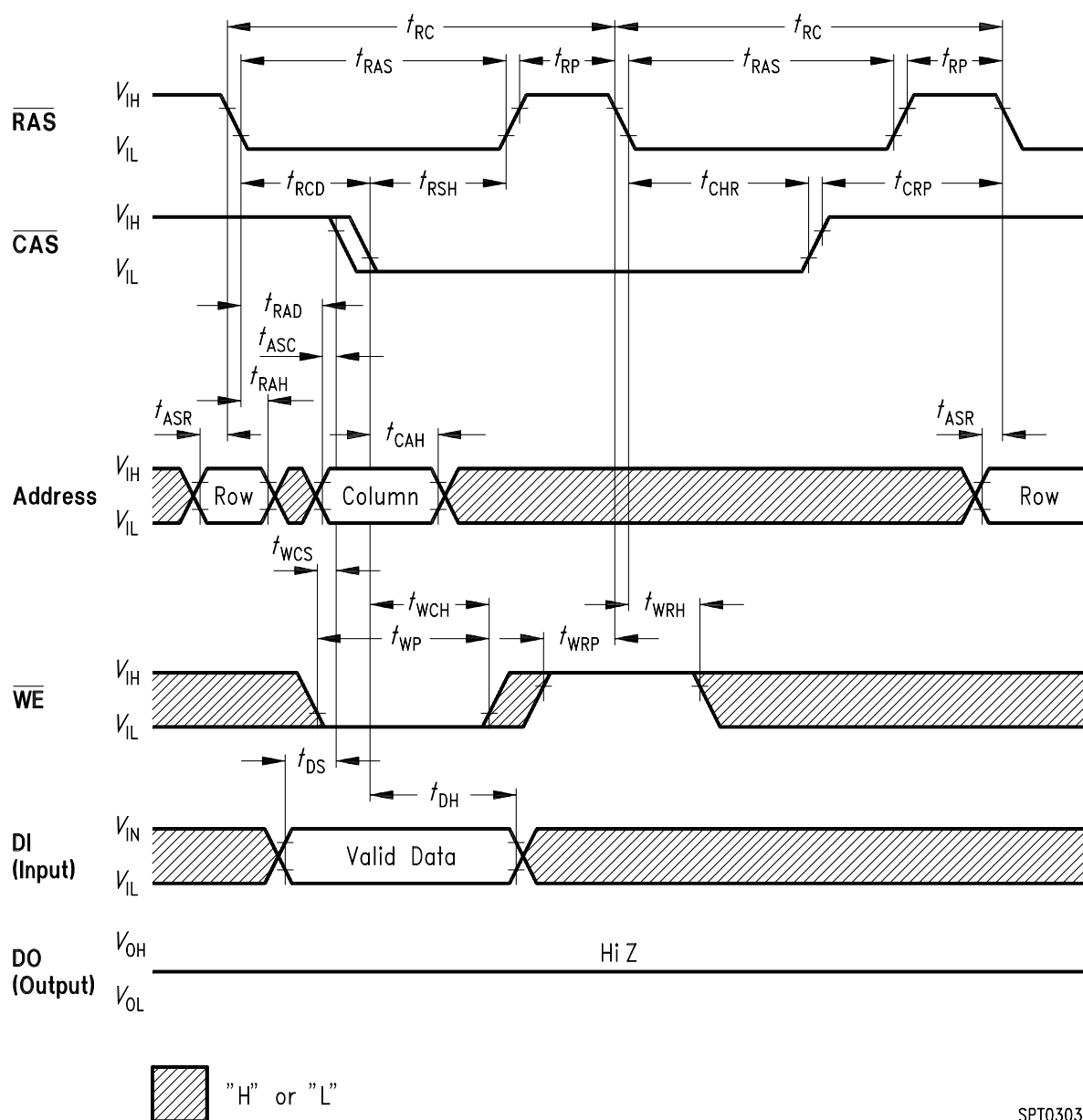
SPT03033

CAS-Before-RAS Refresh Cycle



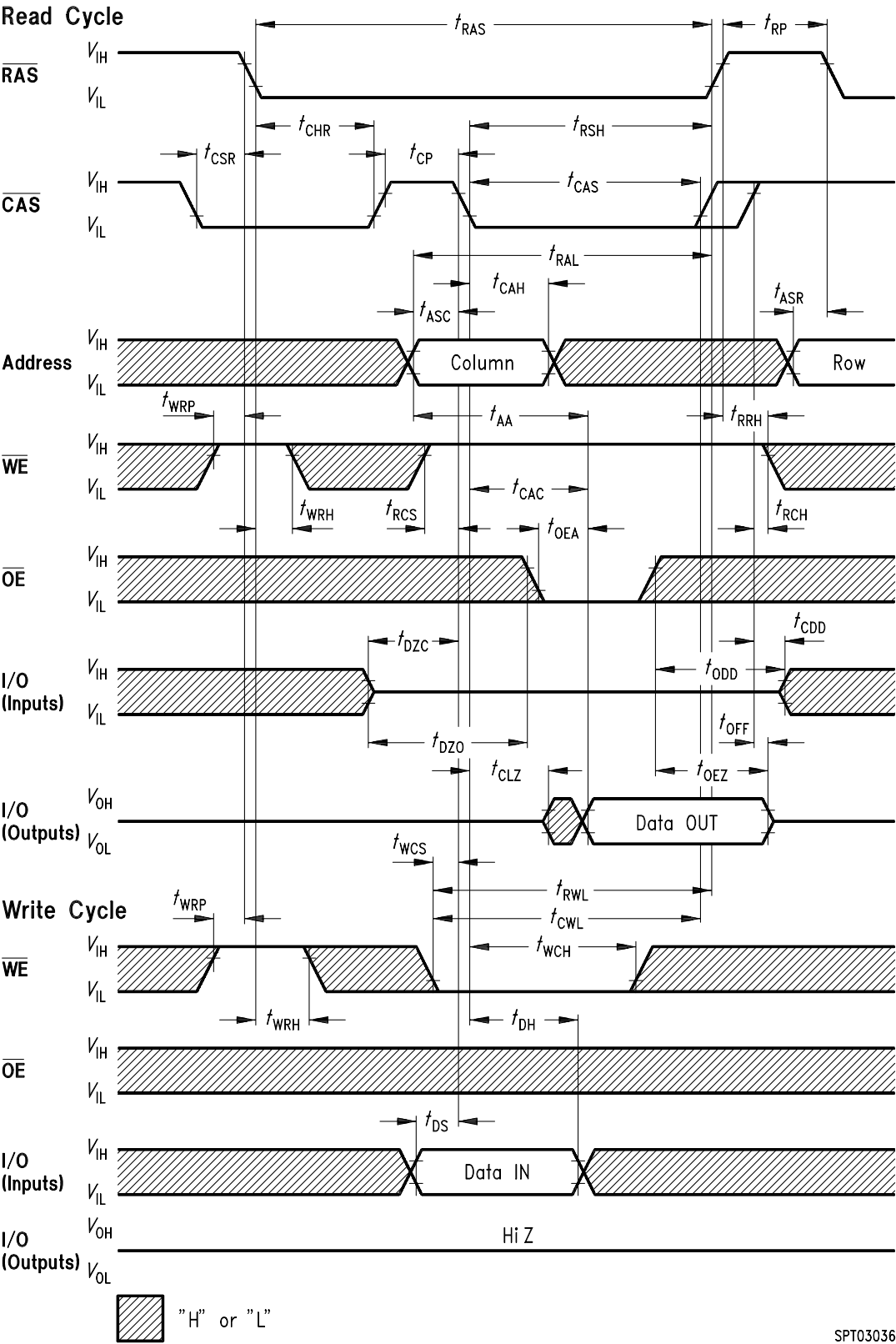
SPT03034

Hidden Refresh Cycle (Read)



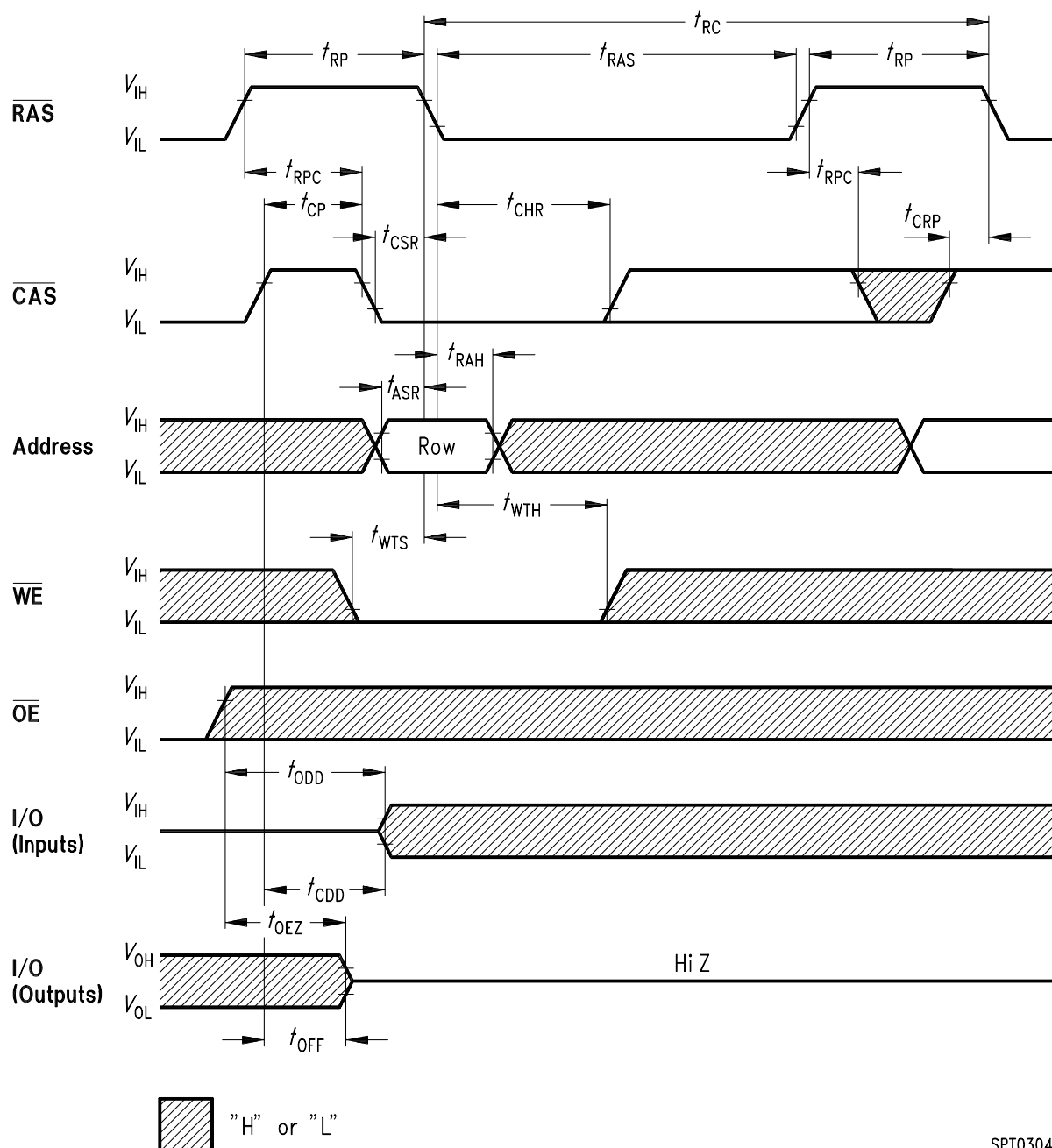
SPT03035

Hidden Refresh Cycle (Early Write)



SPT03036

CAS-Before-RAS Refresh Counter Test Cycle



SPT03042

Test Mode Entry

Test Mode

As the HYB 314400BJ/BJT is organized internally as 512 K x 8-bits, a test mode cycle using 8:1 compression can be used to improve test time. Note that in the 1 M x 4 version the test time is reduced by 1/2 for a linear test pattern.

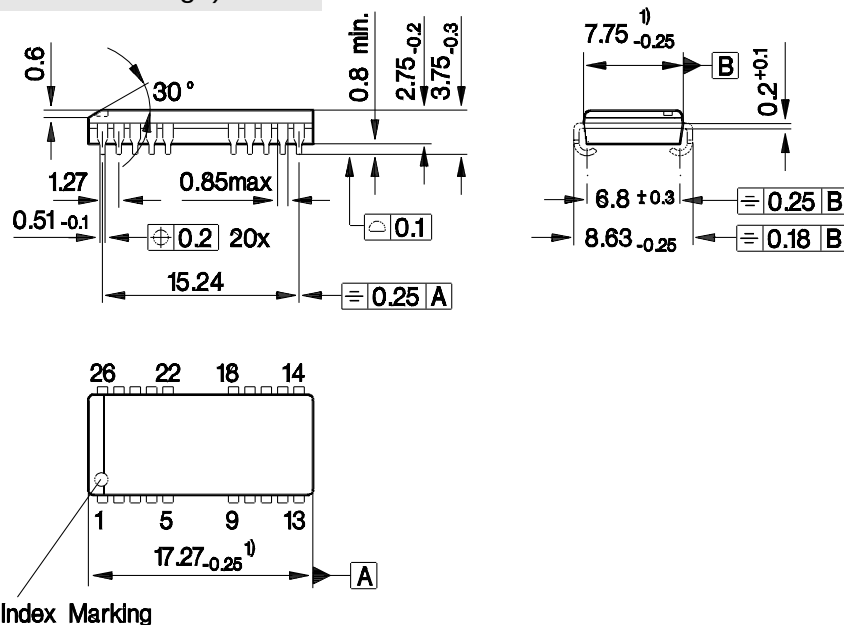
In a test mode "write" the data from each I/O1 pin is written into eight bits simultaneously (all "1"s or all "0"s). The I/O2-I/O4 inputs are not used for writing in test mode. In test mode "read" each I/O output is used for indicating the test mode result. If the internal eight bits are equal, the I/O would indicate a "1". If they were not equal, the I/O would indicate a "0". Note that in test mode "read" I/O1-I/O3 are always driven to "ones", i.e. all outputs will be "1"s for a test mode "pass". The WCBR cycle ($\overline{\text{WE}}$, $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$) puts the device into test mode. To exit from test mode, a " $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh", " $\overline{\text{RAS}}$ only refresh" or "Hidden refresh" can be used.

Addresses A10R, A10C and A0C are don't care during test mode.

Package Outlines

P-SOJ-26/20-5

(Small Outline J-Leaded Package)



Index Marking

1) Does not include plastic or metal protrusion of 0.15 max. per side

GPJ05627

Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".

SMD = Surface Mounted Device

Dimensions in mm